

#### Monolithic dual diode transient voltage suppressor in bare die form

#### Features:

- Configures as x2 unidirectional or x1 bidirectional (x2 wire)
- Very low leakage
- Low capacitance
- 5V stand-off voltage
- High reliability tested grades.

# Ordering Information

The following part suffixes apply:

- No suffix MIL-STD-750 /2073 Visual Inspection
- "H" MIL-STD-750 /2073 Visual Inspection + MIL-PRF-38534 Class H LAT
- "K" MIL-STD-750 /2073 Visual Inspection + MIL-PRF-38534 Class K LAT

LAT = Lot Acceptance Test.

For further information on LAT process flows see below.

www.siliconsupplies.com\quality\bare-die-lot-qualification

## Supply Formats:

- Default Die in Waffle Pack (400 per tray capacity)
- Sawn Wafer on Tape By specific request
- Unsawn Wafer By specific request
- Die Thickness <> 230µm(9 Mils) On request
- With additional electrical selection On request

### Die Dimensions in µm (mils)



#### CHIP BACK MUST BE CONNECTED TO ANODE

#### NOTE:

THIS MONOLITHIC CHIP COMPRISES X2 UNIDIRECTIONAL TVS DIODES WITH COMMON ANODE CONNECTION.

## **Mechanical Specification**

Die Size (Unsawn)	290 x 350 11.42 x 13.78	µm mils	
Cathode Pad Size	90 x 90 3.54 x 3.54	µm mils	
Die Thickness	230 (±15) 9.05 (±0.59)	µm mils	
Top Metal Composition	Al		
Back Metal Composition	Si		



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# Absolute Maximum Ratings<sup>1</sup> $T_J = 25^{\circ}C$ unless otherwise stated

PARAMETER	SYMBOL	VALUE	UNIT
Peak Pulse Power (t <sub>p</sub> = 8/20 µs)	Рек	140	W
Peak Pulse Current (t <sub>p</sub> = 8/20 µs)		11	Δ
Peak Pulse Current (t <sub>p</sub> = 5/50 ns)		40	~
Operating Junction temperature	TJ	-55 to 175	°C
Storage Temperature Range	T <sub>STG</sub>	-65 to 200	°C

1. Operation above the absolute maximum rating may cause device failure. Operation at the absolute maximum ratings, for extended periods, may reduce device reliability.

#### ESD Rating Compliant to IEC 61000-4-2

PARAMETER	SYMBOL	VALUE	UNIT
Air	V <sub>ESD</sub>	±30	kV
Contact		±30	kV

#### Electrical Characteristics T<sub>J</sub> = 25°C unless otherwise stated

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT
Reverse Stand-Off Voltage	V <sub>RWM</sub>		-	-	5	V
Reverse Breakdown Voltage	V <sub>BR</sub>	I <sub>T</sub> = 1mA	6.5	-	8.5	V
Reverse Leakage	I <sub>R</sub>	V <sub>RWM</sub> = 5V	-	2	150	nA
Clamping Voltage	Va	I <sub>PP</sub> = 5A, t <sub>p</sub> = 8/20 μs	-	-	9.7	V
	VC	I <sub>PP</sub> = 11A, t <sub>p</sub> = 8/20 μs	-	-	13.6	
Junction Capacitance	C.	$V_R = 0V$ , f = 1MHz	-	25	40	pF
	CJ	V <sub>R</sub> = 2.5V, f = 1MHz	-	20	30	
Reverse Dynamic Resistance	R <sub>DYN, REV</sub>	l== > 2A	-	0.55	-	
Forward Dynamic Resistance	R <sub>DYN, FWD</sub>	1997 27		0.35	-	52



FIGURE 1. Bidirectional Configuration









# ESD Protection Diode – TPD5030

#### Typical Characteristics T<sub>J</sub> = 25°C unless otherwise stated



FIGURE 3. Peak Pulse Power Versus Pulse Duration



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FIGURE 4. Clamp Voltage Versus Peak Pulse Current



FIGURE 5. Junction Capacitance Versus Reverse Voltage

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